

ZXMN6A07F

60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	Max R _{DS(on)}	Max I _D T _A = 25°C (Note 7)
60V	250mΩ@ V _{GS} = 10V	1.4A
607	350 m Ω @ V _{GS} = 4.5 V	1.2A

Description

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed, making it ideal for high-efficiency power management applications.

Applications

- DC-DC converters
- Power management functions
- Relay and solenoid driving
- Motor control

Features

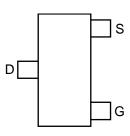
- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate charge
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

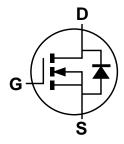
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.008 grams (approximate)



Top View



Top View Pin Out



Equivalent Circuit

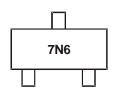
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A07FTA	AEC-Q101	7N6	7	8	3000
ZXMN6A07FQTA	Automotive	7N6	7	8	3000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information



7N6 = Product Type Marking Code



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Units	
Drain-Source Voltage	Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GS}	±20	V	
Continuous Drain Current	V _{GS} = 10V	$T_A = +25$ °C $T_A = +70$ °C $T_A = +25$ °C	(Note 7) (Note 7) (Note 6)	I _D	1.4 1.1 1.2	А
Pulsed Drain Current (Note 8)			I _{DM}	6.9	A	
Continuous Source Current (Body Diode) (Note 7)			I _S	1	A	
Pulsed Source Current (Body Diode) (Note 8)			I _{SM}	6.9	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

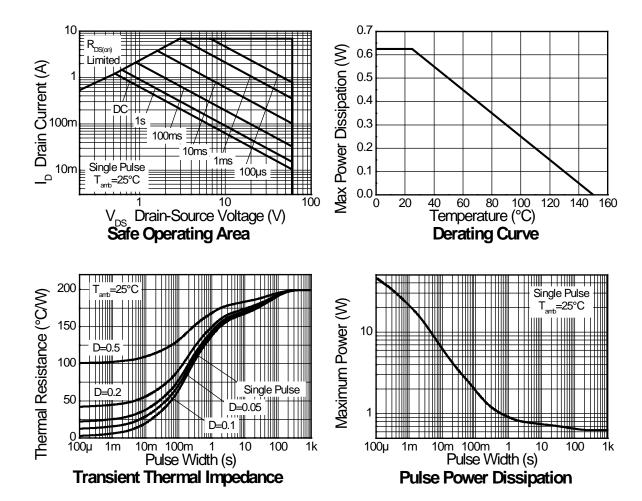
Characteristic	Symbol	Value	Unit	
Power Dissipation (Note 6)	Power Dissipation (Note 6)			mW
Linear Derating Factor	P _D	5	mW/°C	
Power Dissipation (Note 7)	-	806	mW	
Linear Derating Factor	P _D	6.4	mW/°C	
Thermal Desistance, Junction to Ambient	(Note 6)	Б	200	
Thermal Resistance, Junction to Ambient (Note 7)		$R_{\theta JA}$	155	°C/W
Thermal Resistance, Junction to Ambient (Note 9)		$R_{ heta JL}$	194	
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +150	°C	

Notes:

- 6. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 7. For a device surface mounted on FR4 PCB measured at t ≤5 secs.
 8. Repetitive rating 25mm x 25mm FR4 PCB, D=0.02 pulse width=300µs pulse current limited by maximum junction temperate.
- 9. Thermal resistance from junction to solder-point (at the end of the drain lead).



Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

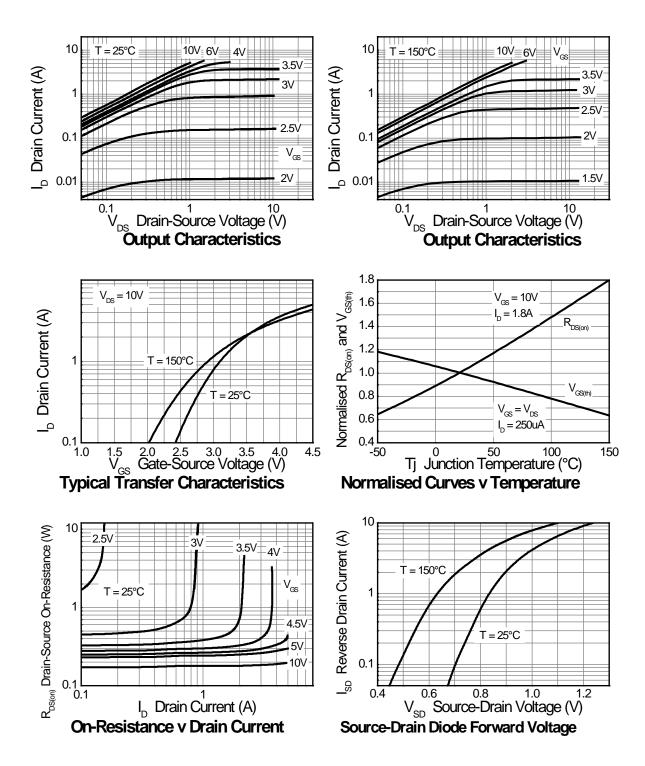
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV_{DSS}	60	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	1.0		3.0	V	$I_D = 250\mu A$, $V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 10)	В			0.250	Ω	$V_{GS} = 10V, I_{D} = -1.8A$	
Static Drain-Source On-Resistance (Note 10)	R _{DS (ON)}	_	_	0.350	12	$V_{GS} = 4.5V, I_D = -1.3A$	
Forward Transconductance (Notes 10 and 12)	g fs	_	2.3	_	S	$V_{DS} = 15V, I_{D} = 1.8A$	
Diode Forward Voltage (Note 10)	V_{SD}	_	0.8	0.95	V	$T_J = +25^{\circ}C$, $I_S = 0.45A$, $V_{GS} = 0V$	
Reverse Recovery Time (Note 12)	t _{rr}	_	20.5	_	ns	$T_J = +25^{\circ}C$, $I_F = 1.8A$,	
Reverse Recovery Charge (Note 12)	Q_{rr}		21.3	_	nC	di/dt = 100A/μs	
DYNAMIC CHARACTERISTICS (Note 12)							
Input Capacitance	C _{iss}	_	166	_		V _{DD} = 40V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss	_	19.5	_	рF		
Reverse Transfer Capacitance	C _{rss}	_	8.7	_			
Turn-On Delay Time (Note 11)	t _{D(on)}	_	1.8	_			
Turn-On Rise Time (Note 11)	t _r	_	1.4	_		$V_{DD} = 30V$, $I_D = 1.8A$, $R_G \cong 6.0\Omega$, $V_{GS} = 10V$	
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	4.9	_	ns		
Turn-Off Fall Time (Note 11)	t _f	_	2.0	_			
Total Gate Charge (Note 11)	Q_g	_	1.65	_	nC	$V_{DS} = 30V, V_{GS} = 5V,$ $I_{D} = 1.8A$	
Total Gate Charge (Note 11)	Qg	_	3.2	_			
Gate-Source Charge (Note 11)	Q_{gs}	_	0.67	_	nC	$V_{DS} = 30V, V_{GS} = 10V,$	
Gate-Drain Charge (Note 11)	Q _{gd}	_	0.82	_		$I_D = 1.8A$	

Notes:

^{10.} Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.
11. Switching characteristics are independent of operating junction temperature.
12. For design aid only, not subject to production testing.

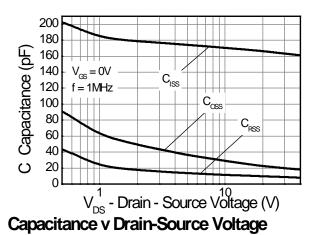


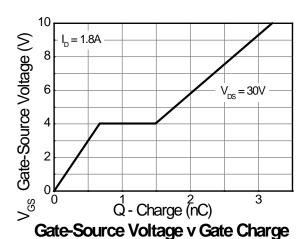
Typical Characteristics



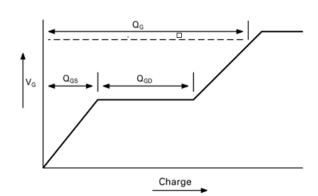


Typical Characteristics - continued

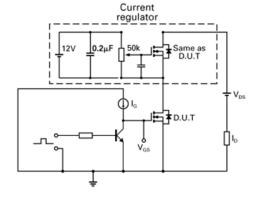




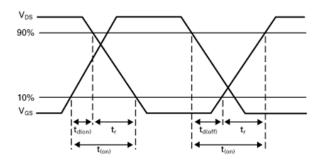
Test Circuits



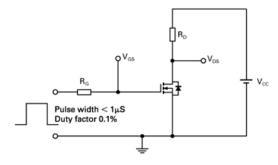
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

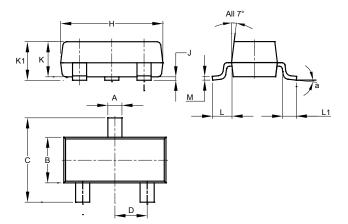


Switching time test circuit



Package Outline Dimensions

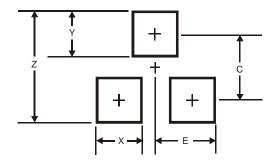
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
M	0.085	0.150	0.110		
а	8°				
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	2.9		
Х	0.8		
Υ	0.9		
С	2.0		
E	1 25		



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